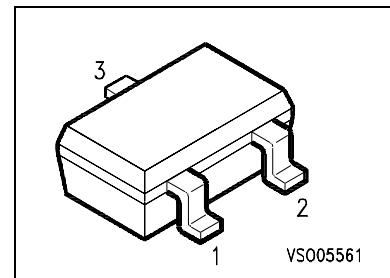


**NPN Silicon AF Transistor**

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary types: BC 807W, BC 808W (PNP)



Type	Marking	Ordering Code (tape and reel)	Pin Configuration			Package
			1	2	3	
BC 817-16W	6As	Q62702-C2320	B	E	C	SOT-323
BC 817-25W	6Bs	Q62702-C2278				
BC 817-40W	6Cs	Q62702-C2321				
BC 818-16W	6Es	Q62702-C2322				
BC 818-25W	6Fs	Q62702-C2323				
BC 818-40W	6Gs	Q62702-C2324				

**Maximum Ratings**

Parameter	Symbol	BC 817W	BC 818W	Unit
Collector-emitter voltage	$V_{CEO}$	45	25	V
Collector-base voltage	$V_{CBO}$	50	30	V
Emitter-base voltage	$V_{EBO}$		5	V
Collector current	$I_C$		500	mA
Collector peak current	$I_{CM}$		1	A
Base current	$I_B$		100	mA
Total Power dissipation $T_S=130^\circ\text{C}$	$P_{tot}$		250	mW
Junction temperature	$T_j$		150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-65 to +150		$^\circ\text{C}$

**Thermal Resistance**

Junction-ambient 1)	$R_{th JA}$	$\leq 215$	K/W
Junction-soldering point	$R_{th JS}$	$\leq 80$	K/W

1) Package mounted on epoxy pcb 40mm x 40mm x 1.5mm/0.5cm<sup>2</sup> Cu.

**Electrical Characteristics**at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Value			Unit
		min.	typ.	max.	

**DC Characteristics**

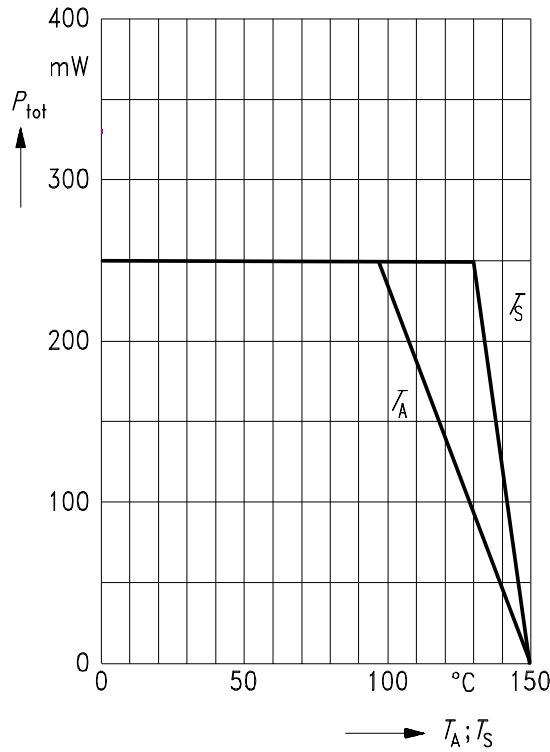
Collector-emitter breakdown voltage $I_C = 10 \text{ mA}$ BC 817W BC 818W	$V_{(\text{BR})\text{CEO}}$	45 25	- -	- -	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}$ BC 817W BC 818W	$V_{(\text{BR})\text{CBO}}$	50 30	- -	- -	V
Emitter-base breakdown voltage $I_E = 10 \mu\text{A}$	$V_{(\text{BR})\text{EBO}}$	5	-	-	V
Collector-base cutoff current $V_{CB} = 25 \text{ V}$ $V_{CB} = 25 \text{ V}, T_A = 150^\circ\text{C}$	$I_{CBO}$	-	-	100 5	nA $\mu\text{A}$
Emitter cutoff current $V_{EB} = 4 \text{ V}$	$I_{EBO}$	-	-	100	nA
DC current gain $I_C = 100 \text{ mA}, V_{CE} = 1 \text{ V}$ BC 817-16W... BC 818-16W BC 817-25W... BC 818-25W BC 817-40W... BC 818-40W	$h_{FE}$	100 160 250	160 250 350	250 400 630	-
$I_C = 300 \text{ mA}, V_{CE} = 1 \text{ V}$ BC 817-16W... BC 818-16W BC 817-25W... BC 818-25W BC 817-40W... BC 818-40W		60 100 170	- - -	- - -	
Collector-emitter saturation voltage <sup>1)</sup> $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	$V_{CE\text{sat}}$	-	-	0.7	V
Base-emitter saturation voltage <sup>1)</sup> $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	$V_{BE\text{sat}}$	-	-	1.2	V

**AC Characteristics**

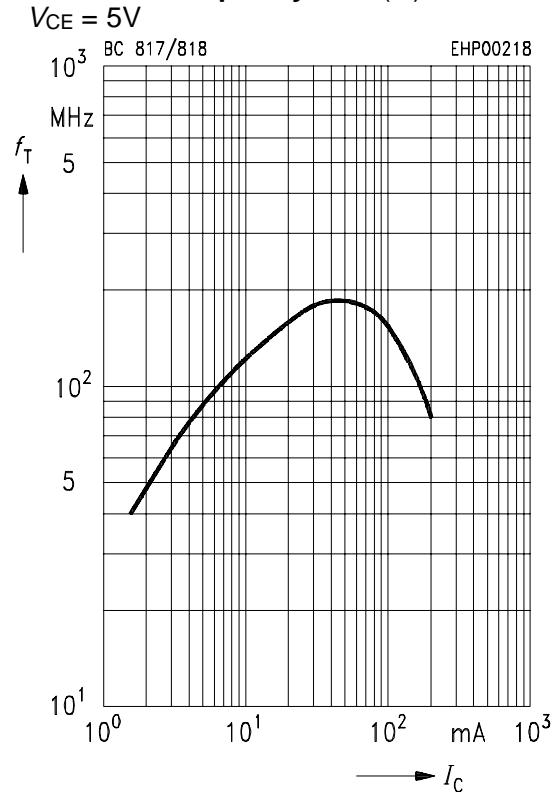
Transition frequency $I_C = 50 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	$f_T$	-	170	-	MHz
Output capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	$C_{cb}$	-	6	-	pF
Input capacitance $V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}$	$C_{eb}$	-	60	-	pF

1) Pulse test:  $t \leq 300\mu\text{s}$ ,  $D \leq 2\%$

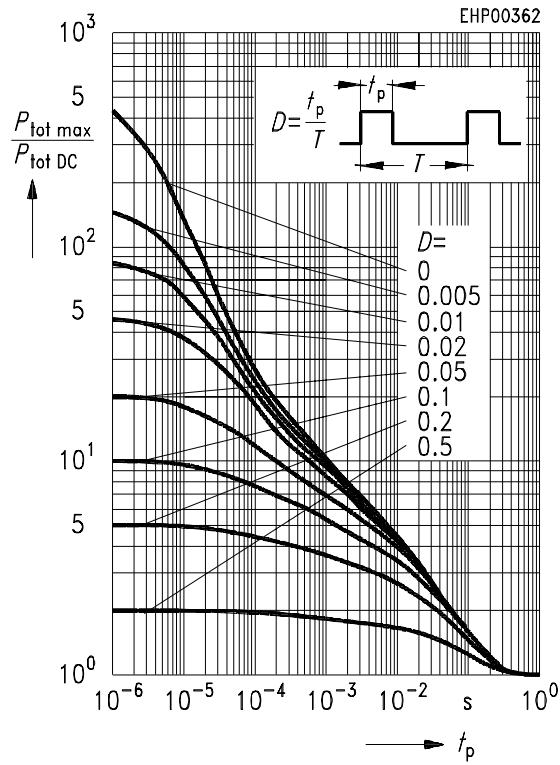
**Total power dissipation**  $P_{\text{tot}} = f(T_A^*; T_S)$   
 \* Package mounted on epoxy



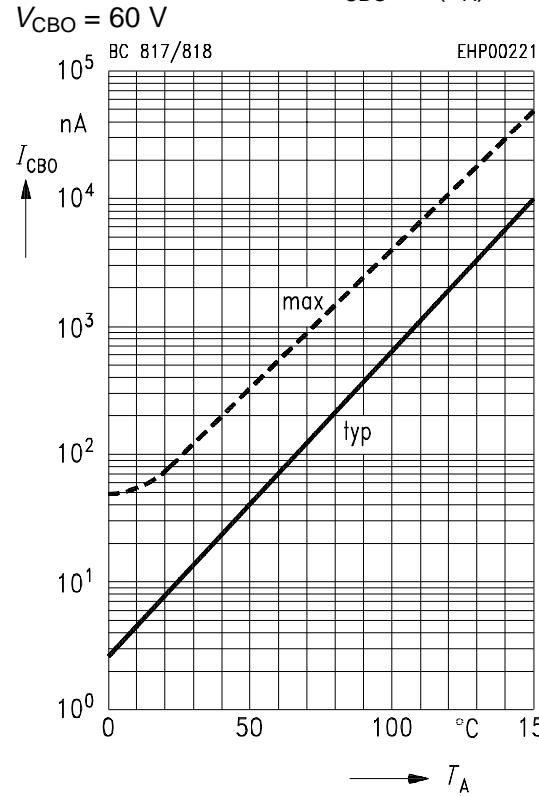
**Transition frequency**  $f_T = f(I_C)$



**Permissible pulse load**  $P_{\text{tot max}}/P_{\text{tot DC}} = f(t_p)$

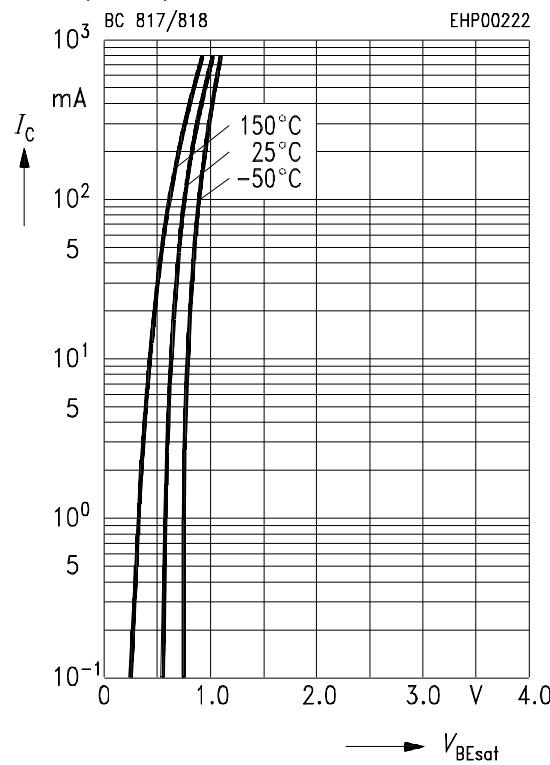


**Collector cutoff current**  $I_{\text{CBO}} = f(T_A)$

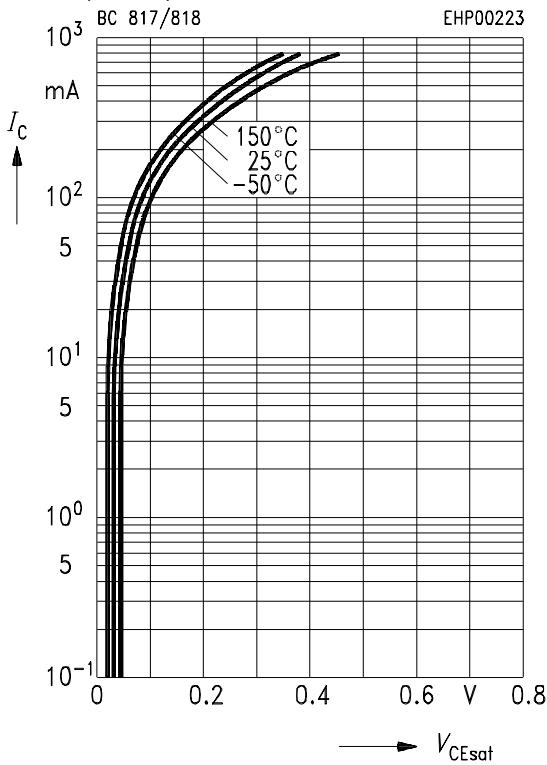


**Base-emitter saturation voltage**

$$I_C = f(V_{BEsat}) \quad h_{FE} = 10$$

**Collector-emitter saturation voltage**

$$I_C = f(V_{CEsat}), \quad h_{FE} = 10$$

**DC current gain  $h_{FE} = f(I_C)$** 

$$V_{CE} = 1V$$

